

### Amendments to the Claims

1. (Original) An electroless Ni-B plating liquid for forming a Ni-B alloy film on at least part of interconnects of an electronic device having an embedded interconnect structure, said electroless Ni-B plating liquid comprising nickel ions, a complexing agent for said nickel ions, a reducing agent for said nickel ions, and ammoniums ( $\text{NH}_4^+$ ).

2. (Original) The electroless Ni-B plating liquid according to claim 1, wherein said reducing agent comprises an alkylamine borane or a hydrogen boride compound.

3. (Original) The electroless Ni-B plating liquid according to claim 1, wherein said ammoniums are prepared from ammonia water.

4. (Original) The electroless Ni-B plating liquid according to claim 1, wherein a pH of said electroless Ni-B plating liquid is adjusted within the range from 8 to 12.

5. (Original) The electroless Ni-B plating liquid according to claim 1, wherein a temperature of said electroless Ni-B plating liquid is adjusted within the range from 50°C to 90°C.

6-11. (Cancel)

12. (Currently amended) A method for manufacturing an electronic device, comprising;

electroless plating an electronic device having an embedded interconnect structure with an electroless Ni-B plating liquid to form a protective layer of a Ni-B alloy film selectively on a surface of an interconnect of said electronic device;

wherein said electroless Ni-B plating liquid comprises nickel ions, a complex agent for nickel ions, a reducing agent for nickel ions, and ~~ammonium~~ ammonium ions ( $\text{NH}_4^+$ ).

13. (Original) The method according to claim 12, wherein said Ni-B alloy film has an FCC crystalline structure.

14. (Original) The method according to claim 12, wherein said Ni-B alloy film has a boron content within the range from 0.01 at% to 10 at%.

15. (New) The method according claim 12, wherein the Ni-B alloy film has a thickness of 0.1 to 500 nm.

16. (New) The method according to claim 12, wherein the Ni-B alloy film has a thickness of 10 to 100 nm.